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(71) Applicant: ADVANCED MICRO DEVICES, INC. [US/US]; One AMD Place, Mail Stop 68, P.O. Box 3453, Snunyvale, CA 94088-3453 (US).

(72) Inventors: AHMED, Shibly, S.; 350 Elan Village Lane, #105, San Jose, CA 95134 (US). WANG, Haihong; 34170 Donahue Terrace, Fremont, CA 94555 (US). YU, Bin; 1373 Poppy Way, Cupertino, CA 95014 (US).

(74) Agent: COLLOPY, Daniel, R.; Advanced Micro Devices, Inc., One AMD Place, Mail Spop 68, Sunnyvale, CA 94088-3453 (US).

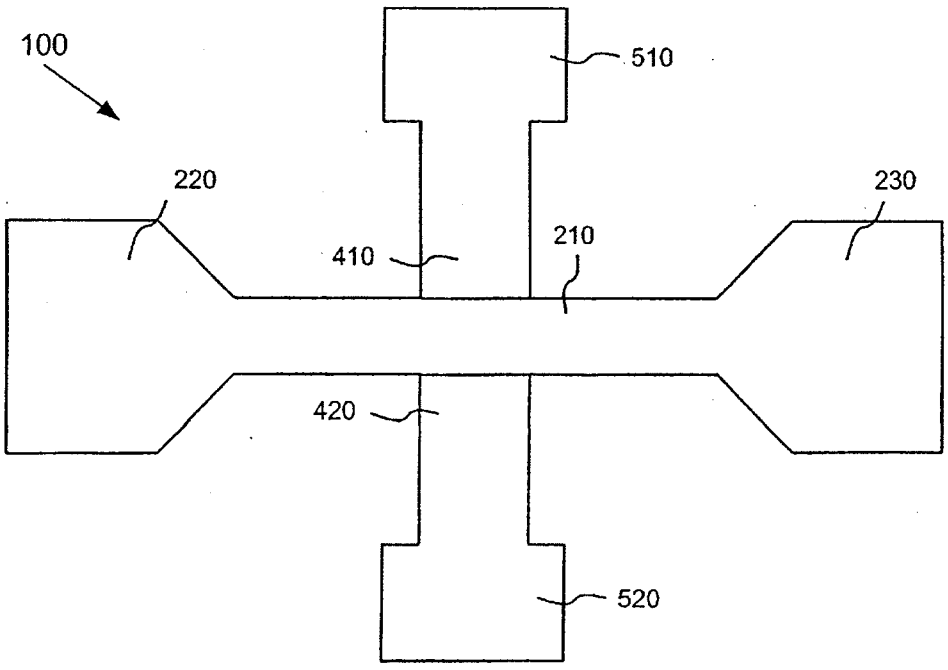
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(54) Title: DOUBLE GATE SEMICONDUCTOR DEVICE HAVING SEPARATE GATES



(57) Abstract: A semiconductor device (100) may include a substrate (110) and an insulating layer (120) formed on the substrate (110). A fin (210) may be formed on the insulating layer (120) and may include a number of side surfaces and a top surface. A first gate (410) may be formed on the insulating layer (120) proximate to one of the number of side surfaces of the fin (210). A second gate (420) and may be formed on the insulating layer (120) separate from the first gate (410) and proximate to another one of number of side surfaces of the fin (210).

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